

# Transient Voltage Suppressor Diode

**BZA109TS**

18 Diode Array

6.8V/100mA

**DATASHEET**

OEM – Philips

Source: Philips Databook 1999

## 9-fold ESD transient voltage suppressor

BZA109TS

## FEATURES

- ESD rating >8 kV, according to IEC1000-4-2
- SOT339-1 surface mount package
- Common anode configuration
- Non-clamping range -0.5 to +6.8 V
- Maximum non-repetitive peak reverse power dissipation: 25 W at  $t_p = 1$  ms
- Maximum clamping voltage at peak pulse current: 10 V at  $I_{ZSM} = 2.5$  A.

## DESCRIPTION

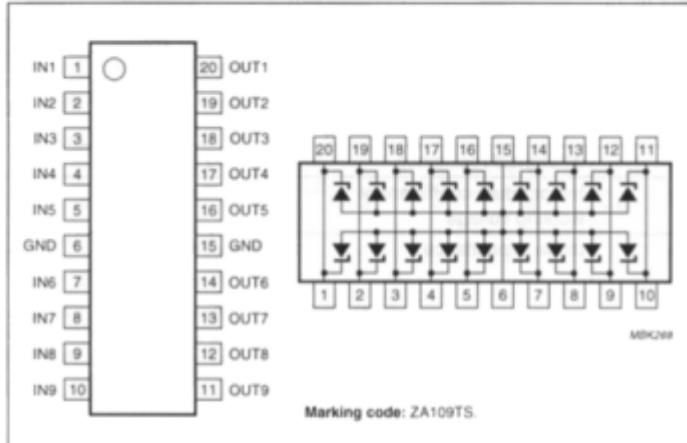
9-fold monolithic transient voltage suppressor in an SSOP20; SOT339-1 surface mount package. The device is ideal in situations where board space is a premium.

## PINNING

PIN	DESCRIPTION
1 to 5	input (IN1 to IN5)
6 and 15	common anode (GND)
7 to 10	input (IN6 to IN9)
11 to 14	output (OUT9 to OUT6)
16 to 20	output (OUT5 to OUT1)

## APPLICATIONS

- For 9-bit wide undershoot/overshoot clamping and fast ESD transient suppression in:
  - Computers and peripherals
  - Audio and video equipment
  - Business machines
  - Communication systems
  - Medical equipment.



Marking code: ZA109TS.

Fig.1 Pin configuration for SSOP20 (SOT339-1) and symbol.

## LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
<b>Per diode</b>					
$I_Z$	working current	$T_{amb} = 25$ °C	–	20	mA
$I_F$	continuous forward current	$T_{amb} = 25$ °C	–	100	mA
$I_{FT}$	feed-through current	$T_{amb} = 25$ °C; note 1	–	100	mA
$I_{FSM}$	non-repetitive peak forward current	$t_p = 1$ ms; square pulse	–	4.5	A
$I_{ZSM}$	non-repetitive peak reverse current	$t_p = 1$ ms; square pulse; see Fig.2	–	2.5	A
$P_{tot}$	total power dissipation	$T_{amb} \leq 25$ °C; note 2; see Fig.3	–	0.95	W
$P_{ZSM}$	non-repetitive peak reverse power dissipation	$t_p = 1$ ms; square pulse; see Fig.4	–	25	W
$T_{stg}$	storage temperature		-65	+150	°C
$T_j$	operating junction temperature		-65	+150	°C

## Notes

1. Current is flowing from input to corresponding output.
2. One or more diodes loaded.

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## THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th,j-a}$	thermal resistance from junction to ambient	one or more diodes loaded	135	K/W

## ELECTRICAL CHARACTERISTICS

 $T_j = 25^\circ\text{C}$  unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
<b>Per diode</b>						
$V_Z$	working voltage	$I_Z = 250 \mu\text{A}$	6.4	6.8	7.2	V
$V_F$	forward voltage	$I_F = 100 \text{ mA}$	—	—	1.1	V
$V_{ZSM}$	non-repetitive peak reverse voltage	$I_{ZSM} = 2.5 \text{ A}; t_p = 1 \text{ ms}$	—	—	10	V
$I_H$	input high current	$V_{IN} = 5.25 \text{ V}$	—	—	0.5	$\mu\text{A}$
$r_{dif}$	differential resistance	$I_Z = 250 \mu\text{A}$	—	—	100	$\Omega$
$S_Z$	temperature coefficient of working voltage	$I_Z = 5 \text{ mA}$	—	3	—	$\text{mV/K}$
$C_d$	diode capacitance	see Fig.5 $V_R = 0; f = 1 \text{ MHz}$ $V_R = 5.25 \text{ V}; f = 1 \text{ MHz}$	—	—	200 100	pF pF

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## GRAPHICAL DATA

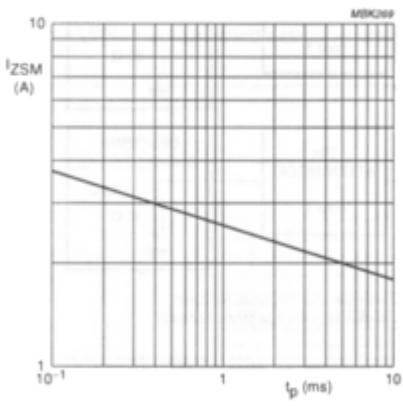
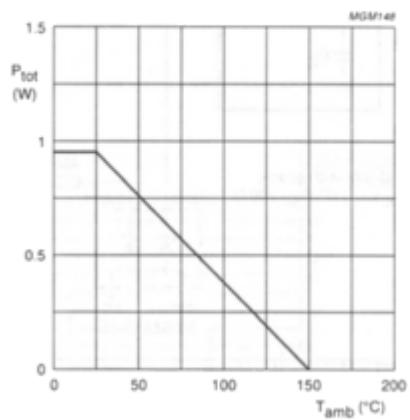
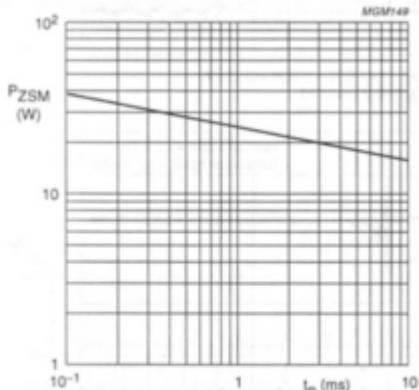


Fig.2 Maximum non-repetitive peak reverse current as a function of pulse time.



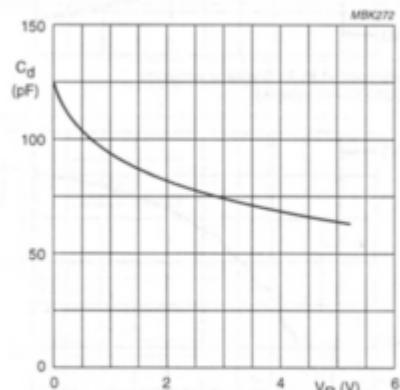
One or more diodes loaded.

Fig.3 Power derating curve.



$P_{ZSM} = V_{ZSM} \times I_{ZSM}$ .  
 $V_{ZSM}$  is the non-repetitive peak reverse voltage at  $I_{ZSM}$ .

Fig.4 Maximum non-repetitive peak reverse power dissipation as a function of pulse duration (square pulse).

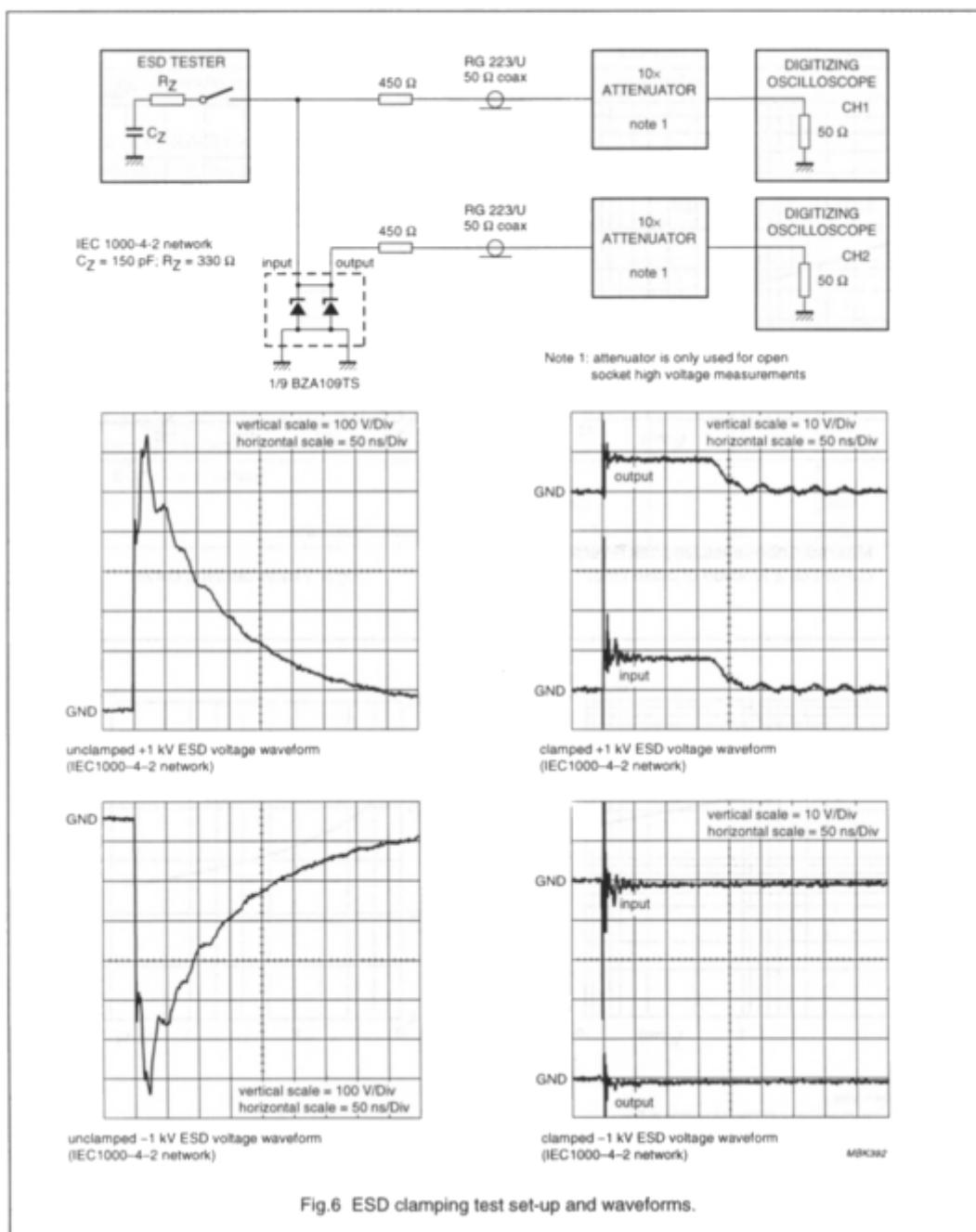


$T_j = 25^\circ\text{C}$ ;  $f = 1\text{ MHz}$ .

Fig.5 Diode capacitance as a function of reverse voltage; typical values.

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**9-fold ESD transient voltage suppressor****BZA109TS****APPLICATION INFORMATION****Typical common anode application**

A 9-fold transient suppressor in an SSOP20; SOT339-1 package makes it possible to protect nine separate lines using only one package. Two simplified examples are shown in Figs 7 and 8.

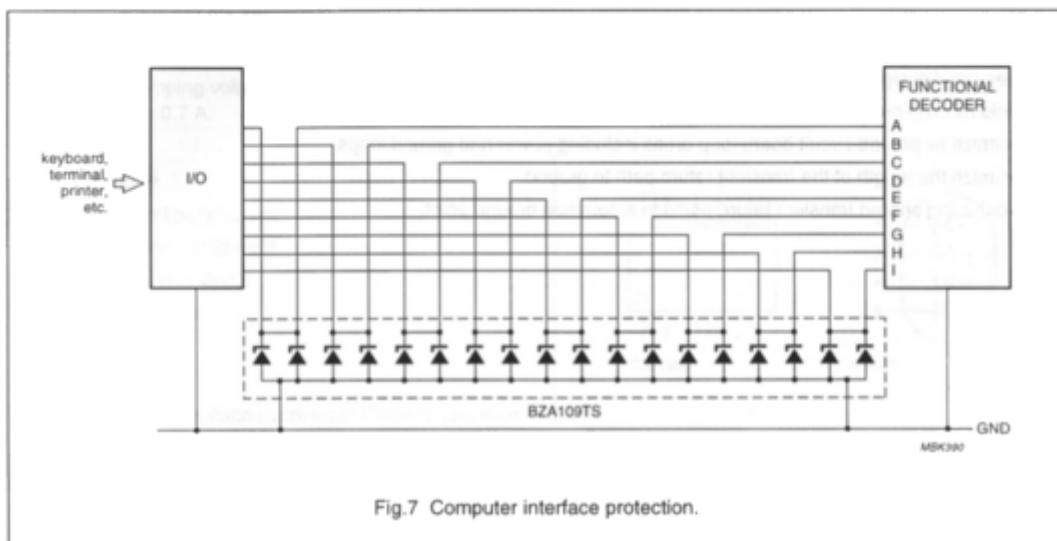


Fig.7 Computer interface protection.

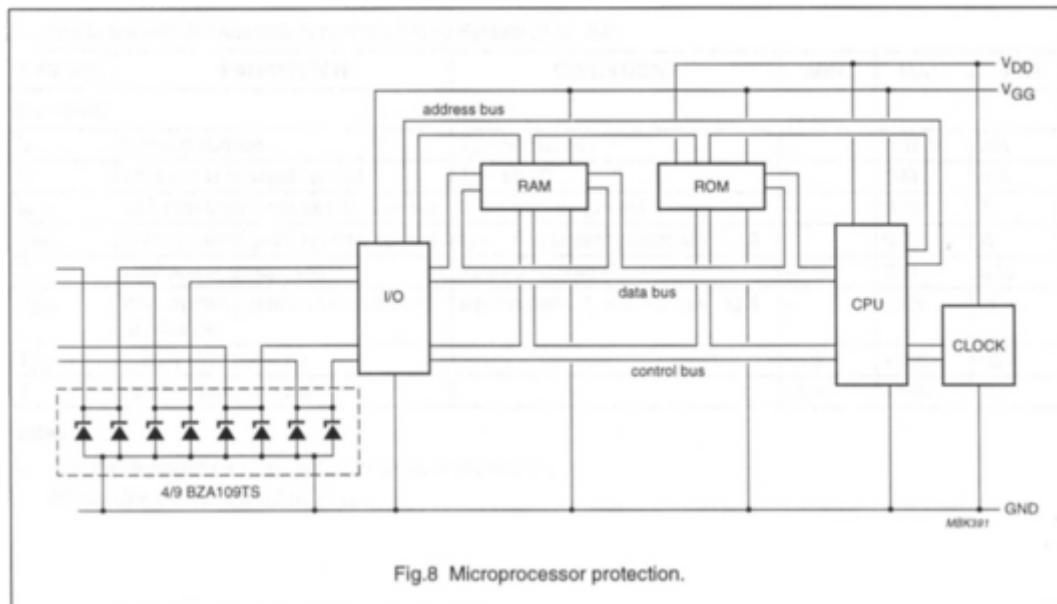


Fig.8 Microprocessor protection.

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**Device placement and printed-circuit board layout**

Circuit board layout is of extreme importance in the suppression of transients. The clamping voltage of the BZA109TS is determined by the peak transient current and the rate of rise of that current ( $di/dt$ ). Since parasitic inductances can further add to the clamping voltage ( $V = L di/dt$ ) the series conductor lengths on the printed-circuit board should be kept to a minimum. This includes the lead length of the suppression element.

In addition to minimizing conductor length the following printed-circuit board layout guidelines are recommended:

1. Place the suppression element close to the input terminals or connectors.
2. Keep parallel signal paths to a minimum.
3. Avoid running protection conductors in parallel with unprotected conductors.
4. Minimize all printed-circuit board loop areas including power and ground loops.
5. Minimize the length of the transient return path to ground.
6. Avoid using shared transient return paths to a common ground point.